

**WHAT IS CLAIMED IS:**

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1. A semiconductor device comprising:  
a substrate;  
a source/drain diffused layer formed in the substrate  
for a transistor; and  
a dummy diffused layer formed in the substrate,  
wherein the source/drain diffused layer has its surface  
silicided, and  
wherein the dummy diffused layer has its surface covered  
with an anti-silicidation film at least partially.

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2. The device of Claim 1, wherein the anti-silicidation  
film is an oxide film.

3. The device of Claim 1, wherein a dopant, which has  
been introduced into the source/drain diffused layer, has not  
been introduced into the dummy diffused layer.

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4. A semiconductor device comprising:  
a substrate;  
a source/drain diffused layer formed in the substrate  
for a transistor; and  
a dummy diffused layer formed in the substrate,  
wherein the source/drain diffused layer has its surface  
silicided, and

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wherein the dummy diffused layer has its surface covered with a dummy gate electrode at least partially, the dummy gate electrode having the same structure as a gate electrode for the transistor.

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5. The device of Claim 4, wherein the dummy diffused layer is located between a circuit block and another circuit block, and

wherein the dummy gate electrode is divided into at least two portions disposed between the two circuit blocks.

6. The device of Claim 4, wherein the dummy gate electrode has a fixed potential level.

7. The device of Claim 4, wherein a dopant, which has been introduced into the source/drain diffused layer, has not been introduced into the dummy diffused layer.

8. A semiconductor device comprising:  
a substrate;  
a source/drain diffused layer formed in the substrate for a transistor; and

a dummy diffused layer formed in the substrate,  
wherein the source/drain and dummy diffused layers have their surfaces silicided, and

wherein a well of a first conductivity type is defined in the substrate, and

wherein the dummy diffused layer is formed in the well and a dopant of a second conductivity type has been introduced into the dummy diffused layer, the second conductivity type being opposite to the first conductivity type.

9. The device of Claim 8, wherein the dummy diffused layer has a fixed potential level.

10. The device of Claim 9, wherein the potential level of the dummy diffused layer is fixed at such a level as applying a reverse bias to a pn junction diode formed by the dummy diffused layer and the well.

11. The device of Claim 9, wherein the dummy diffused layer is divided into multiple portions, and

wherein the portions of the dummy diffused layer are connected together by silicide diffused layer interconnects that have been formed in the same layer as the dummy diffused layer.

12. A semiconductor device comprising:

a substrate of a first conductivity type;

a source/drain diffused layer, which is formed in the

substrate for a transistor and has its surface silicided;

a first well of a second conductivity type, the first well being defined in the substrate, the second conductivity type being opposite to the first conductivity type;

a dummy diffused layer formed in the first well and located between two circuit blocks; and

a second well of the first conductivity type, the second well being defined between the first well and one of the two circuit blocks.

13. The device of Claim 12, wherein potential levels of the first and second wells are fixed at such levels as applying a reverse bias to a pn junction diode formed by the first and second wells.

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